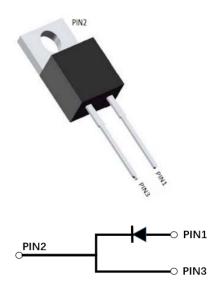
YJD112015PQG3Q

Silicon Carbide Schottky Diode

V_{RRM}	1200V
I _{F (135°C)}	20A
Q _C	91nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- AEC-Q101 qualified
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

Package: TO-220AC
Molding compound meets UL 9

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

• Terminals: Tin plated leads

• Polarity: As marked

■Maximum Ratings (T_C=25°C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D112015PQG3
Reverse voltage (Repetitive peak) @ T _j =25°C	V_{RRM}	٧	1200
Reverse voltage (Surge peak) @ T _j =25°C	V_{RSM}	V	1200
Reverse voltage (DC) @ T _j =25°C	V _{DC}	V	1200
Continuous forward current @ T _C =25°C			44
Continuous forward current @ T _C =135°C	I _F	А	20
Continuous forward current @ T _C =150°C			15
Non-repetitive peak forward surge current @ T _C =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	160
Power Dissipation@ T _C =25°C	9	W	170
Power Dissipation@ T _C =110°C	P _{TOT}		73
i²t Value@ T _C =25°C ,tp=10ms	∫ i²dt	A ² S	128
Operating junction and Storage temperature range	T_{j} , T_{stg}	°C	-55 to +175





■Electrical Characteristics

PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.			
E		٧	I _F =15A, T _j =25°C	1.35	1.55			
Forward voltage drop	V _F		I _F =15A, T _j =175°C	1.85	-			
Deverse leakage gurrent	l _R ,			V _R =1200V, T _j =25°C	3	20		
Reverse leakage current		μA	V _R =1200V, T _j =175°C	19	-			
Total capacitive charge	Qc	nC	V_R =800V, T_j =25°C , Q_C = $\int_0^{VR} C(V) dV$	91	-			
	C pF					V _R =0V, f=1MHZ	1280	-
Total capacitance		pF	V _R =400V, f=1MHZ	87	-			
			V _R =800V, f=1MHZ	64	-			
Capacitance Stored Energy	Ec	μJ	V _R =800V	23	-			

■Thermal Characteristics $(T_a=25$ $^{\circ}$ C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{\theta J-C}$	°C W	0.88

■Typical Characteristics

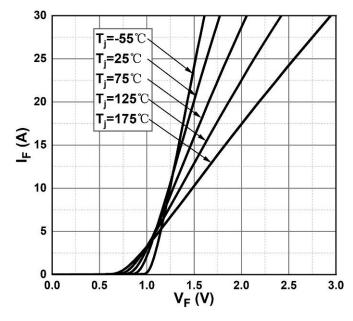


Figure 1. Forward Characteristics

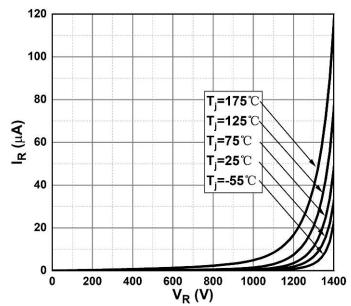
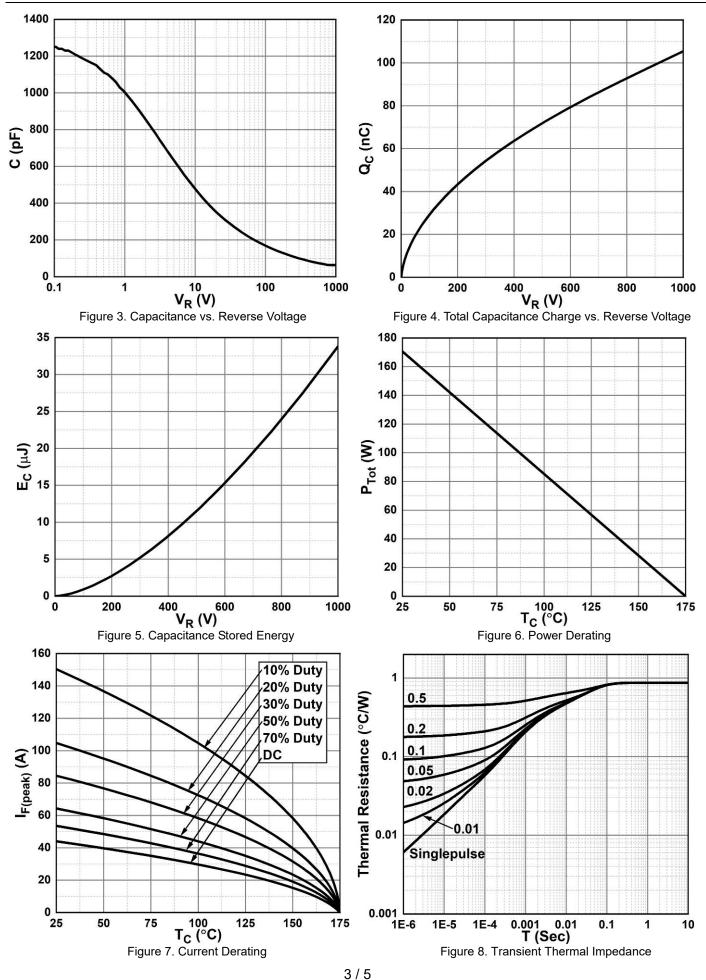


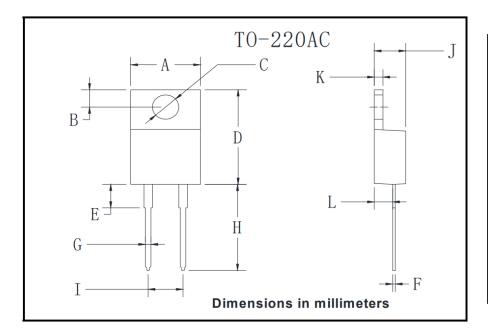
Figure 2. Reverse Characteristics







■Outline Dimensions



TO-220AC				
Dim	Min	Max		
Α	9.95	10.35		
В	2.55	2.95		
С	3.75	4.05		
D	14.95	15.25		
Е	3.75	4.25		
F	0.26	0.5		
G	0.68	0.94		
Н	13.3	13.9		
1	4.86	5.26		
J	4.38	4.78		
K	1.14	1.4		
L	2.37	2.79		



YJD112015PQG3Q



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